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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: J. NOGUCHI, et al.  
Application No.: 09/825,946  
Filed: April 5, 2001  
For: SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE AND  
FABRICATION METHOD FOR SEMICONDUCTOR  
INTEGRATED CIRCUIT DEVICE  
Art Group: 2811  
Examiner: H. Vu

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AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

August 22, 2002

Sir:

In response to the Office Action of May 22, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel Claims 36 and 39 - 41

Please amend Claim 20 as follows:

20. (Amended) A method of fabricating a semiconductor integrated circuit device comprising:

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- (a) providing a semiconductor substrate having a first main surface,
  - (b) forming a first insulating film over said first main surface of said semiconductor substrate,